



P-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	7mΩ @ V _{GS} = -10V	-90A
-30V	16mΩ @ V_{GS} = -4.5 V	-60A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

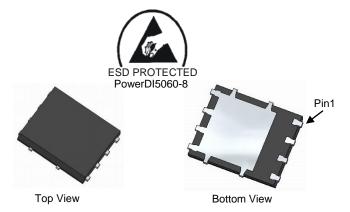
- Backlighting
- Power Management Functions
- DC-DC Converters

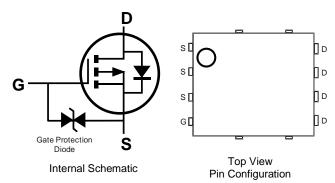
Features and Benefits

- Low R_{DS(ON)} Minimizes On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching Ensures More Reliability
- ESD Protected Gate
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)





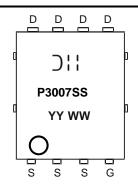
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3007SPS-13	PowerDI5060-8	2,500/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

- 2. See http://www.diodes.com/qual/ity/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦ = Manufacturer's Marking P3007SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±25	V
Continuous Drain Current, V _{GS} = -10V (Note 7)	$T_C = +25$ °C $T_C = +70$ °C	I _D	-90 -70	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	-90	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-160	Α	
Avalanche Current, L=1mH (Note 8)	I _{AS}	-16	Α	
Avalanche Energy, L=1mH (Note 8)	E _{AS}	130	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	90	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 7)	$T_C = +25$ °C	P_{D}	80	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)			•	•	•		
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Otatia Basia Osamas Os Basiatasas	Б	_	4.5	7	0	V _{GS} = -10V, I _D = -15A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	12	16	mΩ	$V_{GS} = -4.5V, I_D = -10A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)	•					•	
Input Capacitance	Ciss	_	2,826	_	pF		
Output Capacitance	Coss	_	606	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	305	_	pF	1 = 1.0MHZ	
Gate Resistance	Rg	_	23	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	31.2	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	64.2	_	nC	V _{DS} = -15V, I _D = -11.5A	
Gate-Source Charge	Q _{gs}	_	10.6	_	nC		
Gate-Drain Charge	Q_{gd}	_	11.6	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.8	_	ns		
Turn-On Rise Time	t _R	_	4.3	_	ns	$V_{DD} = -15V, V_{GS} = -10V,$ $R_g = 6\Omega, I_D = -11.5A$	
Turn-Off Delay Time	t _{D(OFF)}	_	306	_	ns		
Turn-Off Fall Time	t _F	_	125	_	ns		
Reverse Recovery Time	t _{RR}	_	19	_	ns		
Reverse Recovery Charge	Q_{RR}	_	9.8	_	nC	$I_S = -11.5A$, $dI/dt = 100A/\mu s$	

Notes:

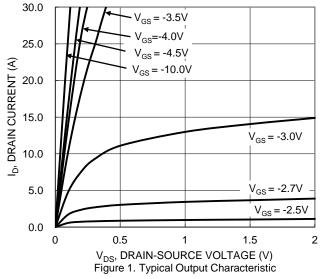
^{5.} Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





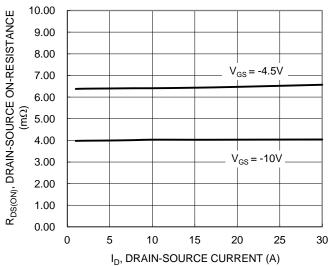


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

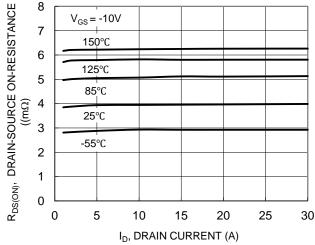


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

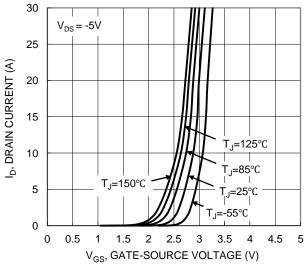
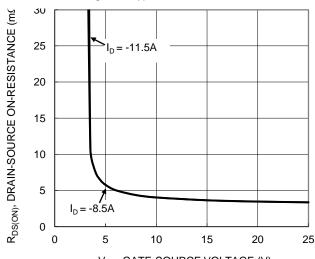


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

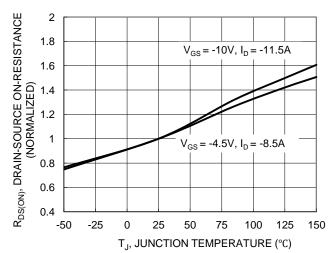


Figure 6. On-Resistance Variation with Temperature





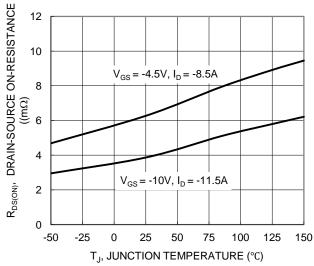


Figure 7. On-Resistance Variation with Temperature

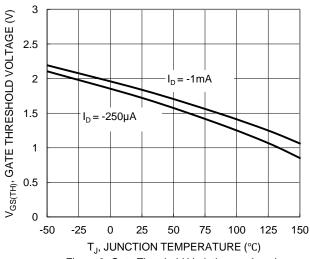
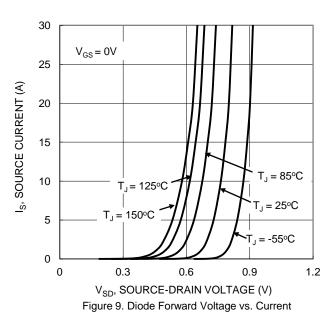


Figure 8. Gate Threshold Variation vs. Junction Temperature



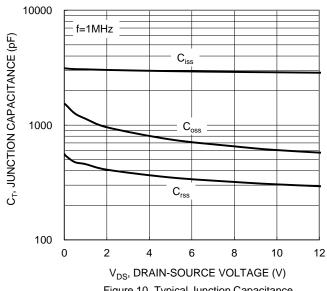
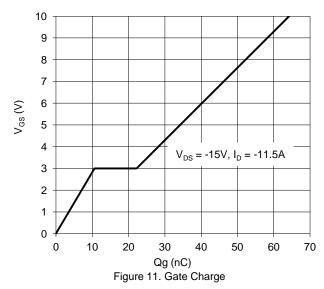


Figure 10. Typical Junction Capacitance



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

=10ms

 $P_W = 100 ms$

10

1000

100

10

0.1

0.1

ID, DRAIN CURRENT (A)

 $R_{\text{DS}(\text{ON})}$ Limited

 $T_{J(Max)} = 150^{\circ}C$

Single Pulse

DUT on on infinite heatsink

T_C = 25°C

 $V_{GS} = -10V$

=10µs P_{W}

1

100



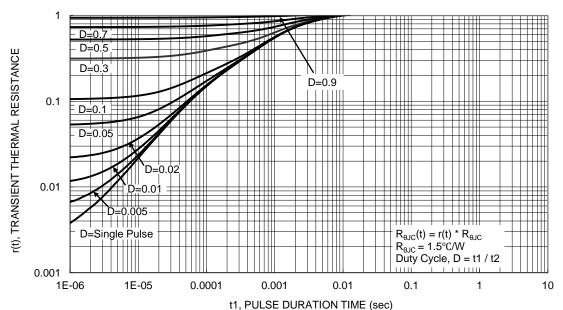


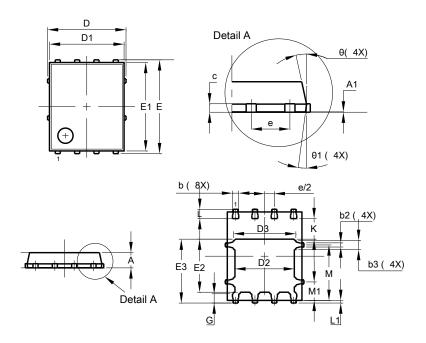
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

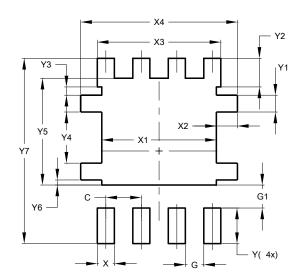


Dim Min Max Typ A 0.90 1.10 1.00 A1 0.00 0.05 − b 0.33 0.51 0.41 b2 0.200 0.350 0.273 b3 0.40 0.80 0.60 c 0.230 0.330 0.277 D 5.15 BSC D1 4.70 5.10 4.90 D2 3.70 4.10 3.90 D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035	PowerDI5060-8				
A 0.90 1.10 1.00 A1 0.00 0.05 − b 0.33 0.51 0.41 b2 0.200 0.350 0.273 b3 0.40 0.80 0.60 c 0.230 0.330 0.277 D 5.15 BSC D1 4.70 5.10 4.90 D2 3.70 4.10 3.90 D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 <th>Dim</th> <th>Min</th> <th>Max</th> <th>Тур</th>	Dim	Min	Max	Тур	
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b2 0.200 0.350 0.273 b3 0.40 0.80 0.60 c 0.230 0.330 0.277 D 5.15 BSC D1 4.70 5.10 4.90 D2 3.70 4.10 3.90 D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°	A1	0.00	0.05	-	
b3 0.40 0.80 0.60 c 0.230 0.330 0.277 D 5.15 BSC D1 4.70 5.10 4.90 D2 3.70 4.10 3.90 D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°	b	0.33	0.51	0.41	
c 0.230 0.330 0.277 D 5.15 BSC D1 4.70 5.10 4.90 D2 3.70 4.10 3.90 D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 -7 0.61 L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 9 10° 12° 11° 91 6° 8° 7°	b2	0.200	0.350	0.273	
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D3 3.90 4.30 4.10 E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 − − L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 9 10° 12° 11° 91 6° 8° 7°		4.70	5.10	4.90	
E 6.15 BSC E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 − − L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 Θ 10° 12° 11° Θ1 6° 8° 7°		3.70	4.10	3.90	
E1 5.60 6.00 5.80 E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 − − L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 Θ 10° 12° 11° Θ1 6° 8° 7°		3.90	4.30	4.10	
E2 3.28 3.68 3.48 E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°		(6.15 BSC	,	
E3 3.99 4.39 4.19 e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°		5.60	6.00	5.80	
e 1.27 BSC G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°		3.28	3.68	3.48	
G 0.51 0.71 0.61 K 0.51 - - L 0.51 0.71 0.61 L1 0.100 0.200 0.175 M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°	E3	3.99	4.39	4.19	
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M 3.235 4.035 3.635 M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°		0.51	0.71	0.61	
M1 1.00 1.40 1.21 O 10° 12° 11° O1 6° 8° 7°		0.100	0.200	0.175	
O 10° 12° 11° O1 6° 8° 7°	M	3.235	4.035	3.635	
O1 6° 8° 7°			1.40		
	Θ	10°			
All Dimensions in mm					
	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	0.755		
Х3	4.420		
X4	5.610		
Y	1.270		
Y1	0.600		
Y2	1.020		
Y3	0.295		
Y4	1.825		
Y5	3.810		
Y6	0.180		
Y7	6.610		



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